

SB5560S 55A SOTs

FEATURES

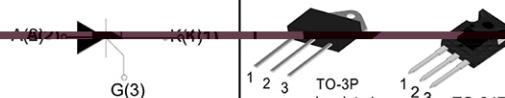
- High thermal cycling performance
- High voltage capacity
- Very high current surge capability

APPLICATIONS

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Parameters Summary

VD/VR:1200/1600V IT(RMS):55A IGT :60mA

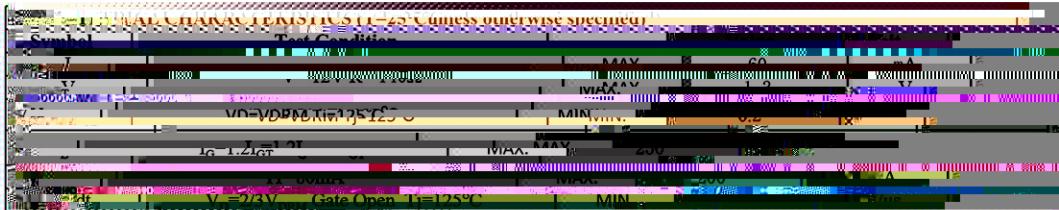


ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T _{stg}	-40 ~ 150	°C
Operating junction temperature range	T _j	-40 ~ 125	°C
Repetitive peak off-state voltage (T=25°C)	V _{DRM}	1200/1600	V
Repetitive peak reverse voltage (T=25°C)	V _{RSM}	1200/1600	V
Non repetitive surge peak Off-state voltage	V _{DSM}	V _{DRM} +100	V
Non repetitive peak reverse voltage	V _{RSM}	V _{RSM} +100	V
RMS on-state current	I _{T(80°C)}	55	A
	I _{T(85°C)}		
Non repetitive surge peak on-state current	I _{TSM}	550	A
Average on-state current (180° conduction angle)	I _{T(AV)}	35	A
I ² t value for fusing (tp=10ms)	I ² t	1500	A ² S
Critical rate of rise of on-state current (I=2×IGT, tr ≤ 100 ns)	di/dt	150	A/μS
Peak gate current	I _{GM}	5	A
Average gate power dissipation	P _{G(AV)}	2	W

Thermal Resistances

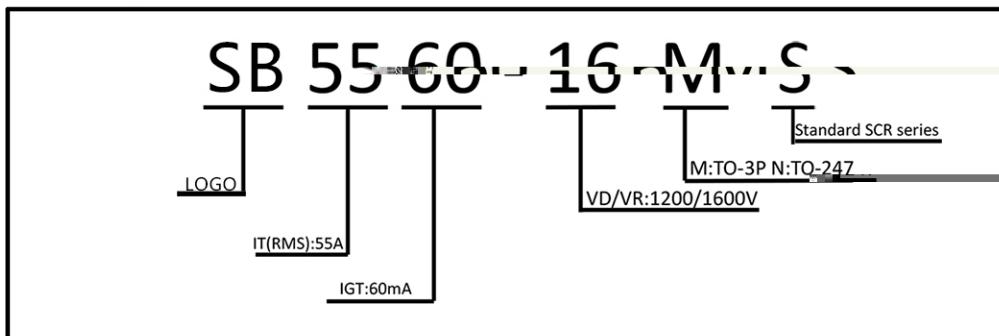
Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (TO-3P)	0.65	°C/W
	TO-247	0.60	°C/W



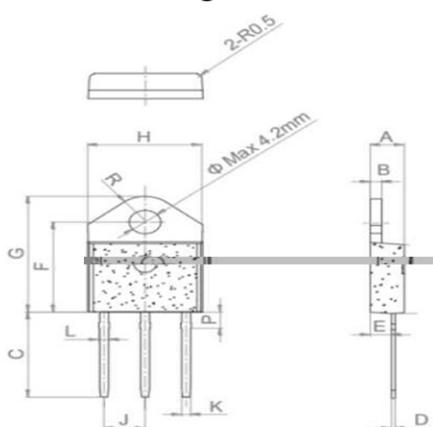
CHARACTERISTICS

Symbol	Parameter	Value (MAX.)	Unit
V_{TM}	V_T (A:D=500ns)	2.0	μV
I_{DRM}	I_{DRM} (A)	1.0	A
I_{RRM}	I_{RRM} (A)	1.0	A

Ordering Information Scheme

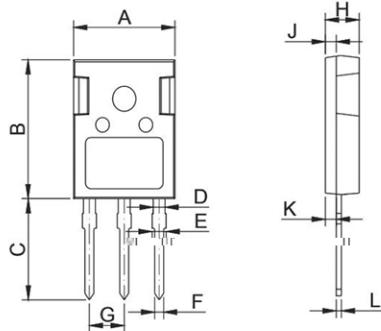


TO-3P Package Mechanical Data



Ref.	Dimension	Value	Unit
A	Height	1.00	inches
B	Width	1.00	inches
C	Length	1.00	inches
D	Max. thickness	0.055	inches
E	Max. width	1.00	inches
F	Max. length	1.00	inches
G	Max. height	0.055	inches
H	Max. width	1.00	inches
I	Max. length	1.00	inches
K	Max. thickness	0.055	inches
L	Max. width	1.00	inches
P	Max. length	2.00	inches
R	Max. thickness	0.055	inches

TO-247 Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	15.90	0.610	0.622	0.634
B	20.80	21.00	22.20	0.815	0.832	0.854
C	19.70	20.00	20.30	0.776	0.787	0.799
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.90	2.10	2.30	0.075	0.083	0.091
F	1.00	1.20	1.40	0.039	0.047	0.055
G		5.44			0.214	0.224
H	4.50	5.00	5.20	0.178	0.197	0.205
J	1.90	2.00	2.10	0.075	0.079	0.083
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.79	0.016	0.024	0.031

FIG.1 Maximum power dissipation versus on-state current

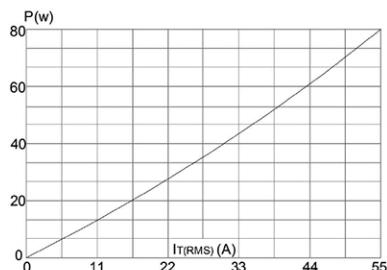


FIG.3: Surge peak on-state current versus number of cycles

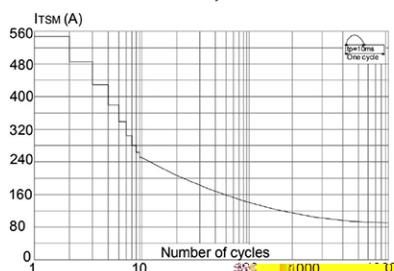


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of $I_2 t$

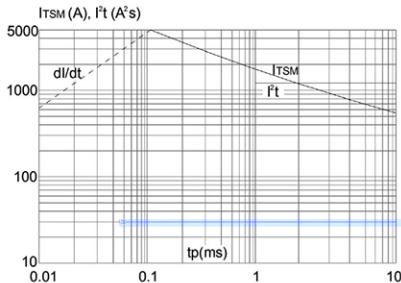


FIG.2: on-state current versus case temperature

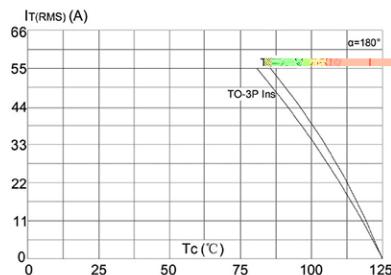


FIG.4: On-state characteristics (maximum values)

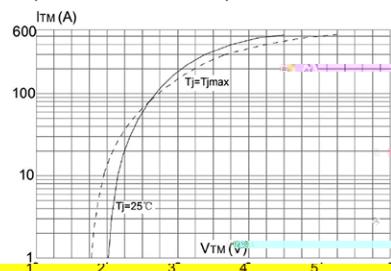


FIG.6: Relative variations of gate current, drain current, drain-to-source current and latching current versus junction temperature

